

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

CPH6444 —

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- Low ON-resistance
- 4V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

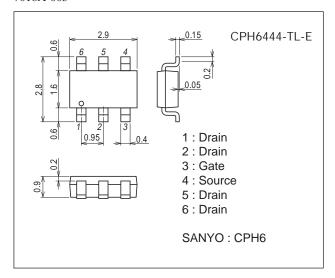
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		4.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	18	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity $< 200 V^*$ ", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ) 7018A-003



Product & Package Information

: CPH6

: SC-74, SOT-26, SOT-457

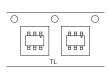
Marking

• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL

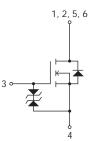
• Package

• JEITA, JEDEC





Electrical Connection



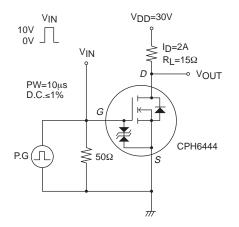
SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

62712 TKIM/22509 MSIM/61808PE TIIM TC-00001431 No. A1243-1/7

Deservation	Symbol	Constituio no		Ratings		
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA 1.2			2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=2A	1.8	3		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=2A, VGS=10V		60	78	mΩ
	R _{DS} (on)2	ID=1A, VGS=4.5V		74	104	mΩ
	R _{DS} (on)3	ID=1A, VGS=4V		81	114	mΩ
Input Capacitance	Ciss			505		pF
Output Capacitance	Coss	VDS=20V, f=1MHz		57		pF
Reverse Transfer Capacitance	Crss			37		pF
Turn-ON Delay Time	t _d (on)			7.3		ns
Rise Time	tr			9.8		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		40		ns
Fall Time	tf			24		ns
Total Gate Charge	Qg			10		nC
Gate-to-Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =4.5A		1.6		nC
Gate-to-Drain "Miller" Charge	Qgd	1		2.1		nC
Diode Forward Voltage	V _{SD}	IS=4.5A, VGS=0V		0.83	1.2	V

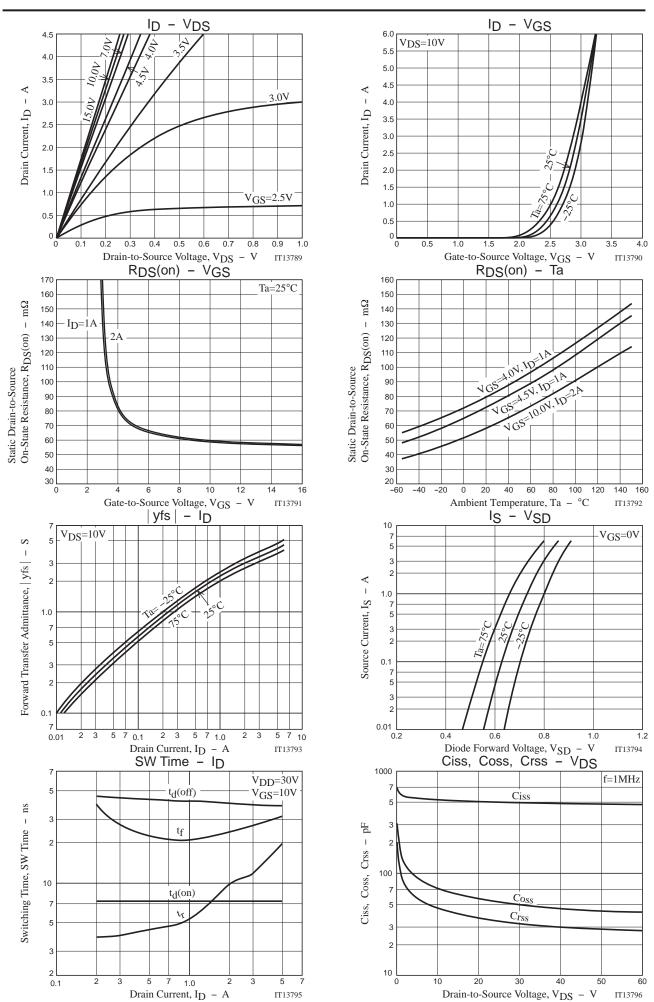
Electrical Characteristics at Ta=25°C

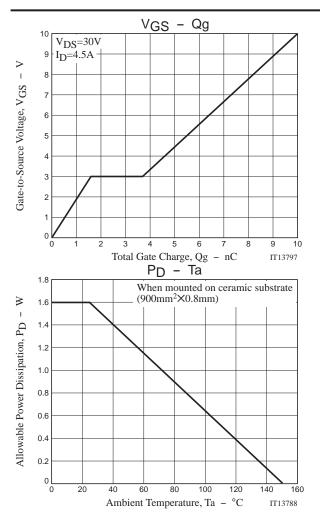
Switching Time Test Circuit

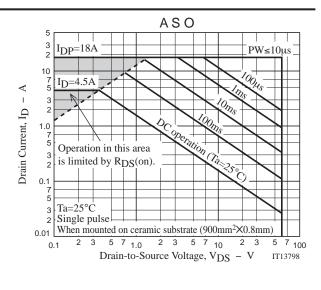


Ordering Information

Device Package		Shipping	memo	
CPH6444-TL-E	CPH6	3,000pcs./reel	Pb Free	







Embossed Taping Specification CPH6444-TL-E

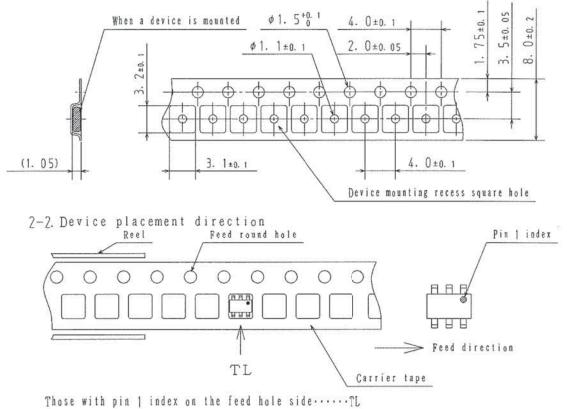
1. Packing Format

LEAD FREE 4

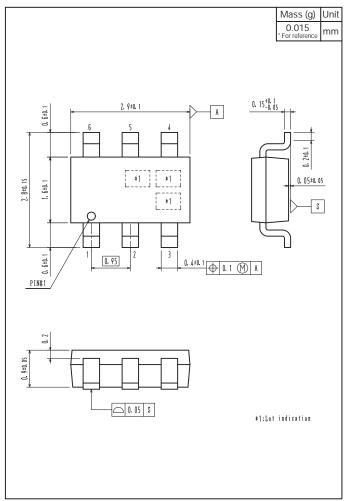
JEITA Phase 3

2. Taping configuration

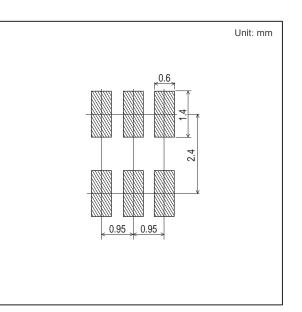
2-1. Carrier tape size (unit:mm)



Outline Drawing CPH6444-TL-E



Land Pattern Example



Note on usage : Since the CPH6444 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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